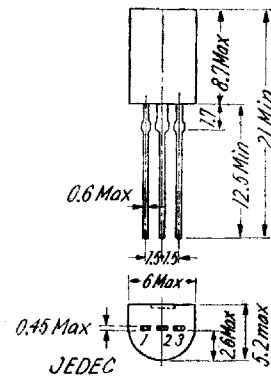


絶対最大定格 Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Characteristics	Symbol	2SK79
Drain-to-Gate Voltage	V_{DG0}	120V
Source-to-Gate Voltage	V_{SG0}	10V
Drain Current	I_D	200mA
Gate Current	I_G	20mA
Total Power Dissipation	P_T	750mW
Junction Temperature	T_j	120°C
Storage Temperature	T_{stg}	-50~+150°C

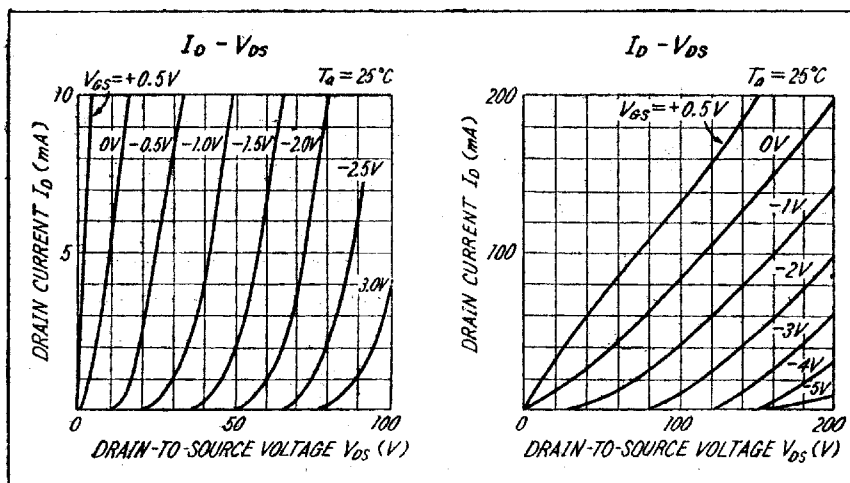


1. Emitter
 2. Base
 3. Collector
- Unit : mm

電気的特性 Electrical Characteristics ($T_a=25^\circ\text{C}$)

Characteristics	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-to-Gate Voltage	V_{DG0}	$I_D=0.1\text{mA}$	120			V
Source-to-Gate Voltage	V_{SG0}	$I_S=0.1\text{mA}$	10			V
Drain Cutoff Current	I_{DG0}	$V_{DG}=50\text{V}, I_S=0\text{A}$			200	nA
Gate Cutoff Current	I_{GSS}	$V_{GS}=6\text{V}, V_{DS}=0\text{A}$			200	nA
Drain-to-Source On-State Voltage	V_{on}	$V_{GS}=0.3\text{V}, I_D=7\text{mA}$			10	V
Pinch-off Voltage	V_P	$V_{DS}=100\text{V}, I_D=300\mu\text{A}$		-4.5	-9.5	V
Voltage Amplification Ratio	μ	$V_{DS}=50\text{V}, I_D=4\text{mA}, f=1\text{kHz}$	15	30		
Forward Transfer Conductance	g_m	$V_{DS}=50\text{V}, I_D=4\text{mA}, f=1\text{kHz}$		14		mS
Input Capacitance	C_{ip}	$V_{DS}=50\text{V}, I_D=4\text{mA}, f=1\text{MHz}$		16		pF
Output Capacitance	C_p	$V_{DS}=50\text{V}, I_D=4\text{mA}, f=1\text{MHz}$		2		k Ω
	C_D			4		pF
Junction-to-Ambient Thermal Resistance	θ_{j-a}				126	°C/W
Noise Figure	NF	$V_{DS}=50\text{V}, I_D=4\text{mA}, R_g=500\text{k}\Omega, f=10\text{Hz}$			30	dB

【第1表】 2SK79 の最大定格と電気的特性



【第19図】 2SK79 の I_D - V_{DS} 特性